

FIG. 1

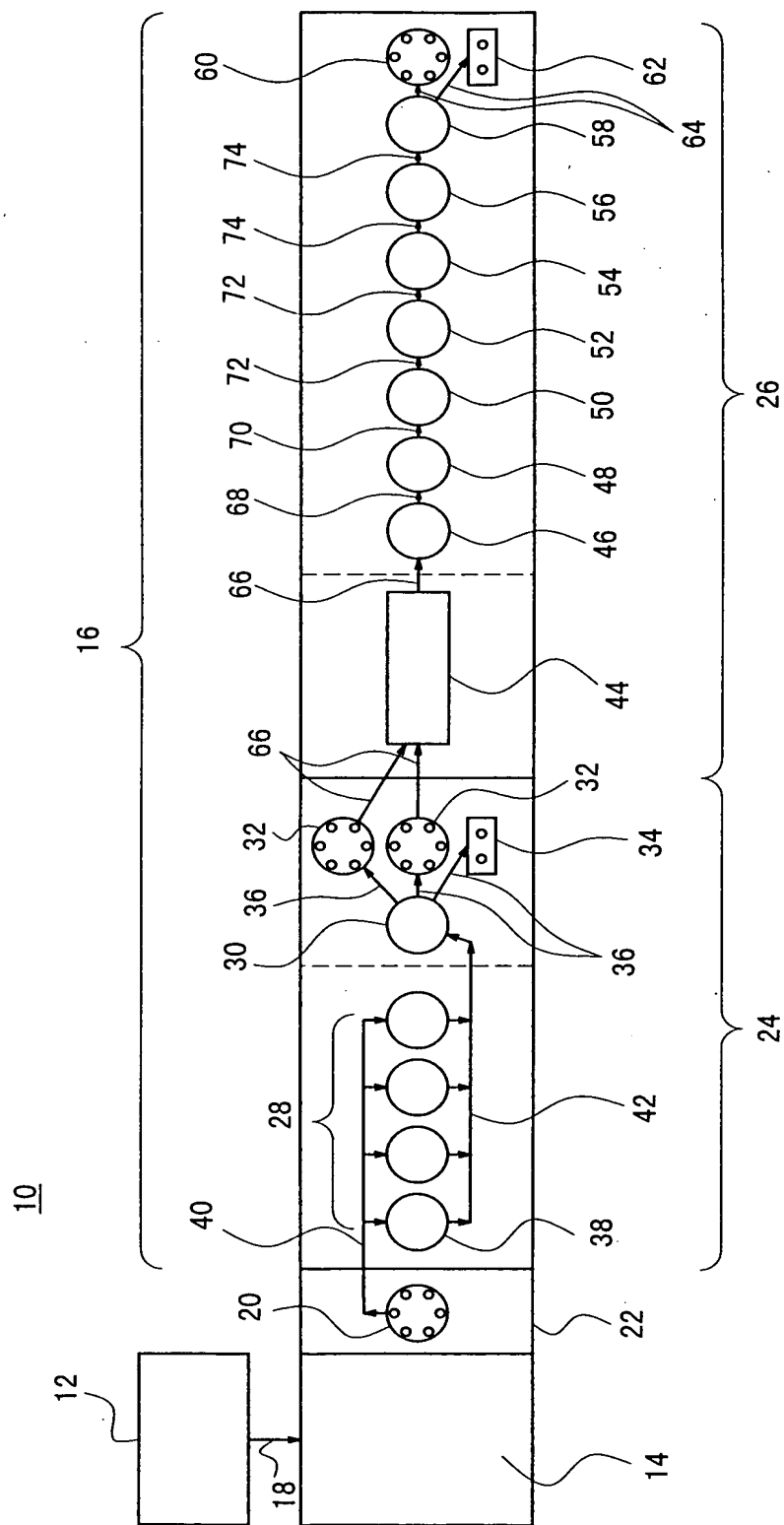
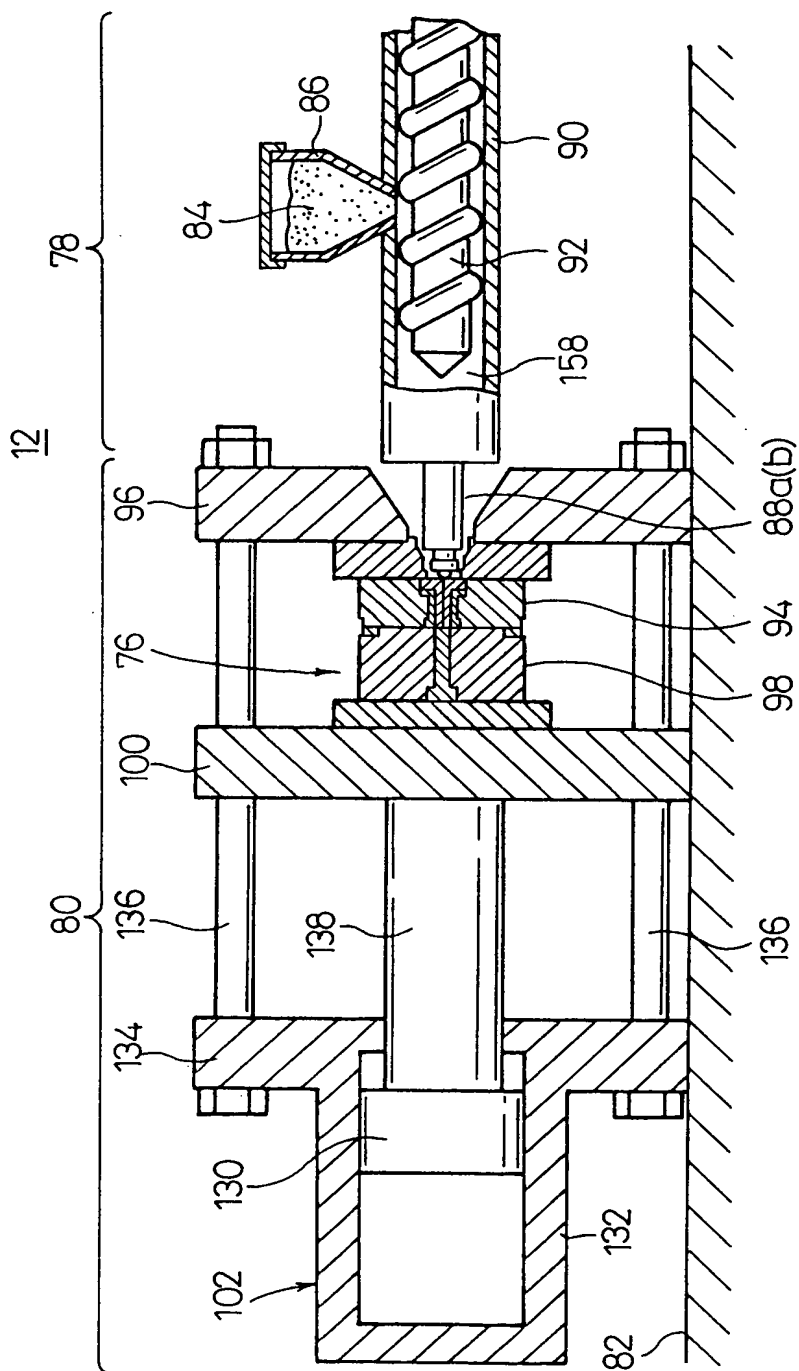


FIG. 2



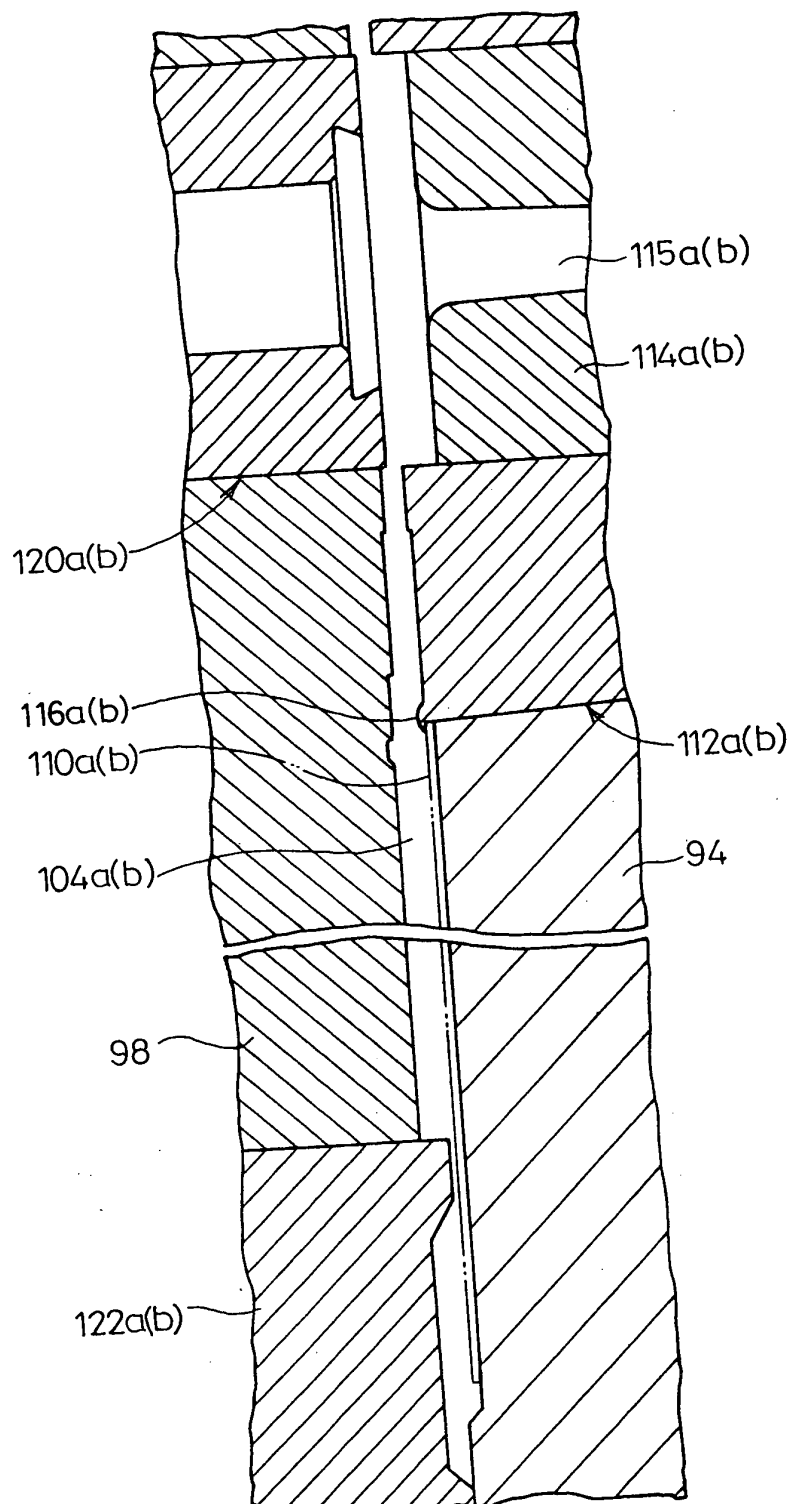
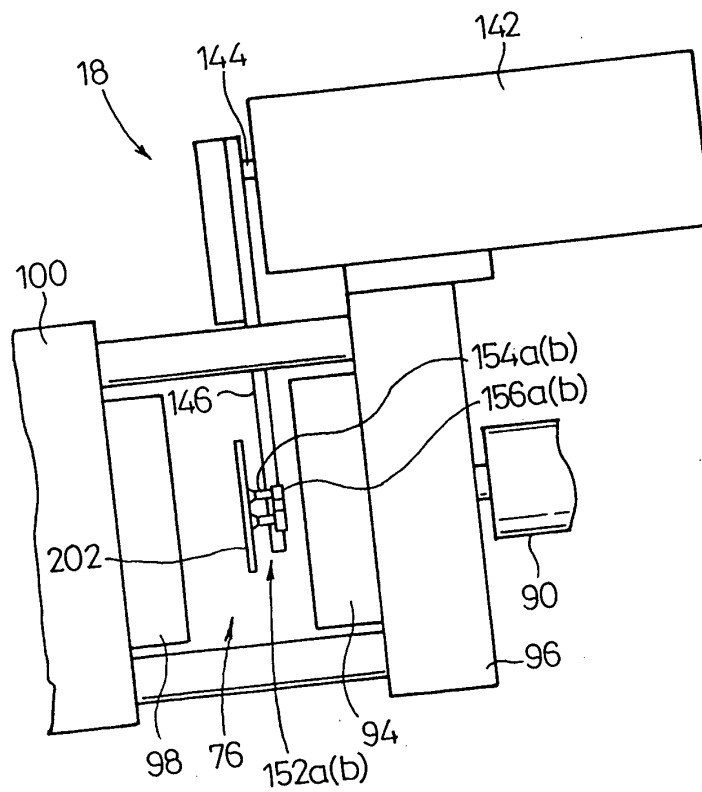
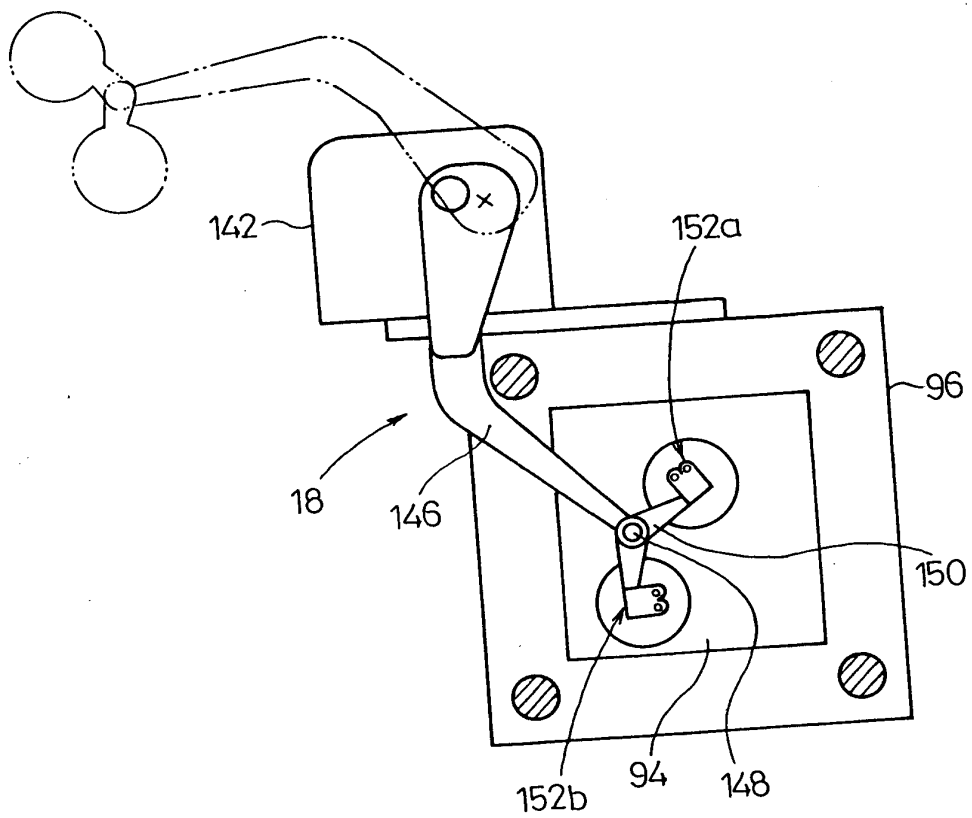


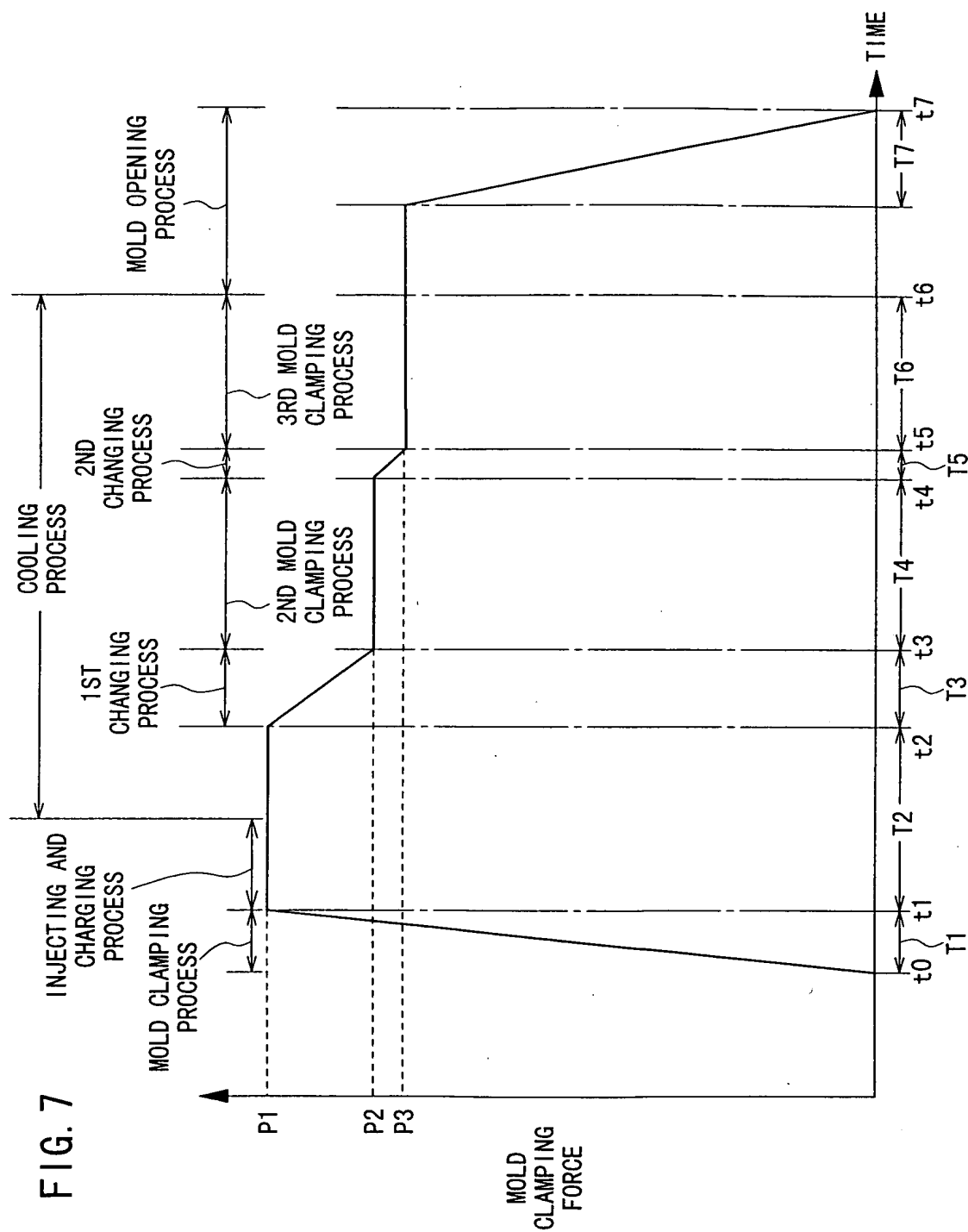
FIG. 5



OFFICE 2F360460

FIG. 6





8/17

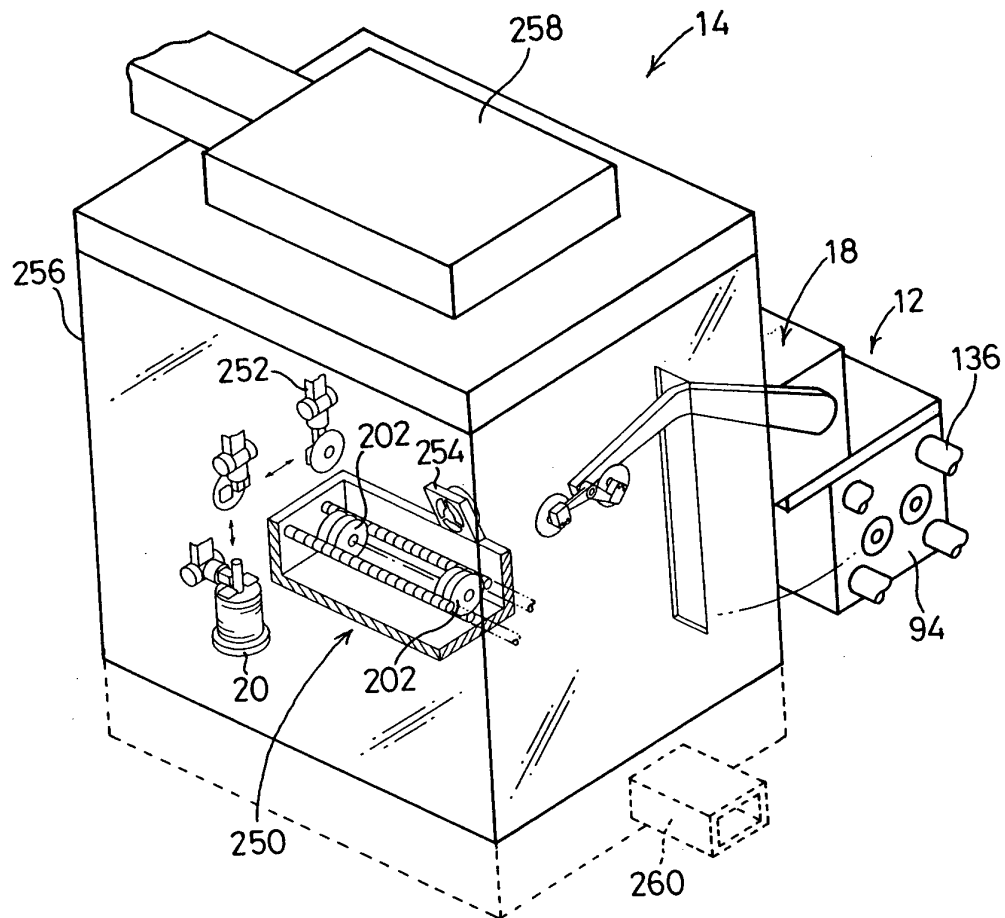


FIG. 10A

FIG. 10A is a cross-sectional view of a substrate 200. The substrate 200 has a series of rectangular protrusions 202 extending from its top surface. A break symbol is shown in the middle of the substrate 200.

FIG. 10B

200 202 204

A cross-sectional view of a semiconductor device. A substrate 200 is shown with a patterned layer 202 on its top surface. The patterned layer 202 consists of a series of rectangular blocks. A layer 204 is deposited on top of the patterned layer 202, filling the spaces between the blocks. A layer 206 is deposited on top of layer 204, forming a continuous top layer. A layer 208 is shown as a thin layer on top of layer 206. A curved line indicates a cross-section through the device.

210 208 204 D 200 202

FIG. 12

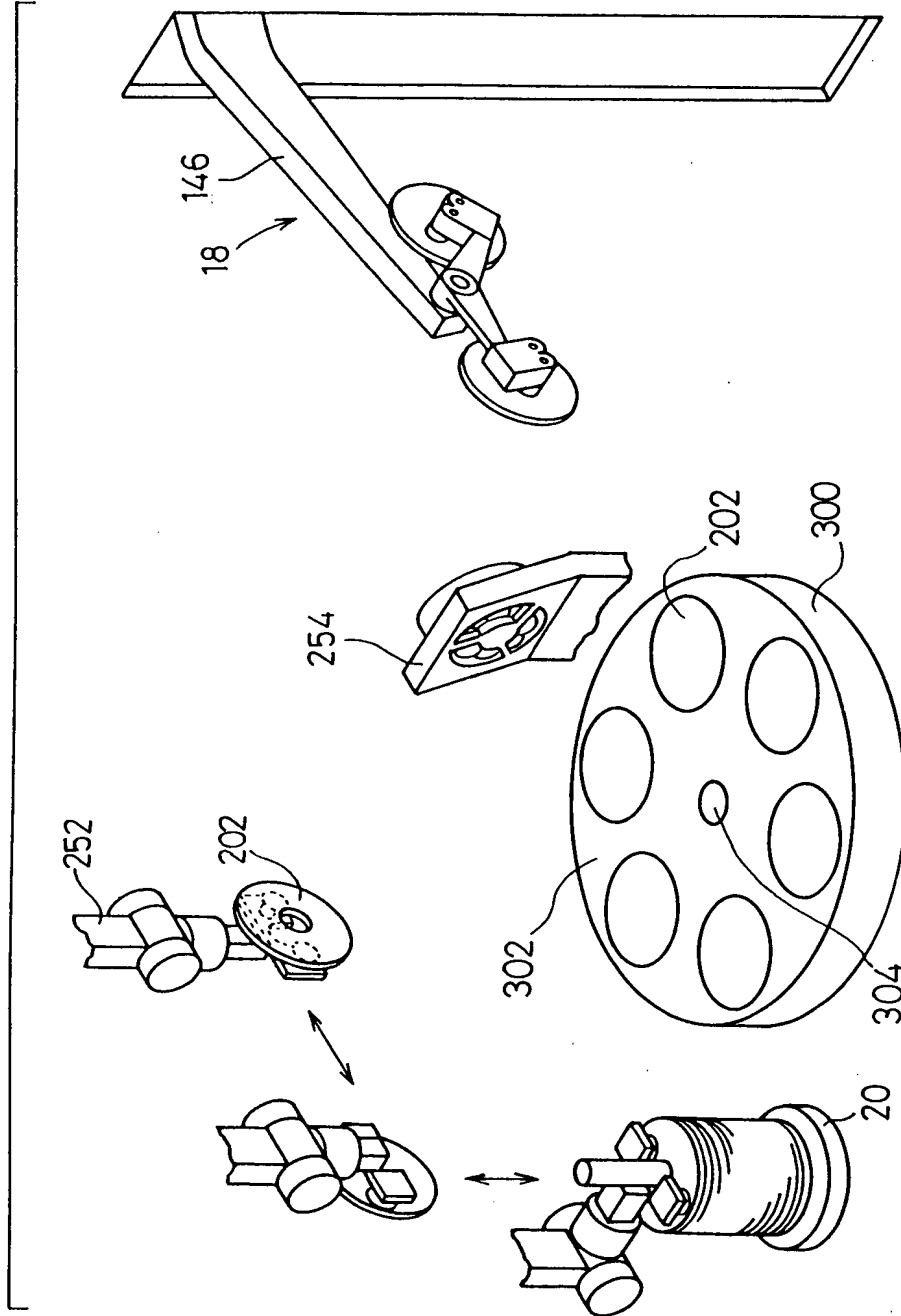


FIG. 13

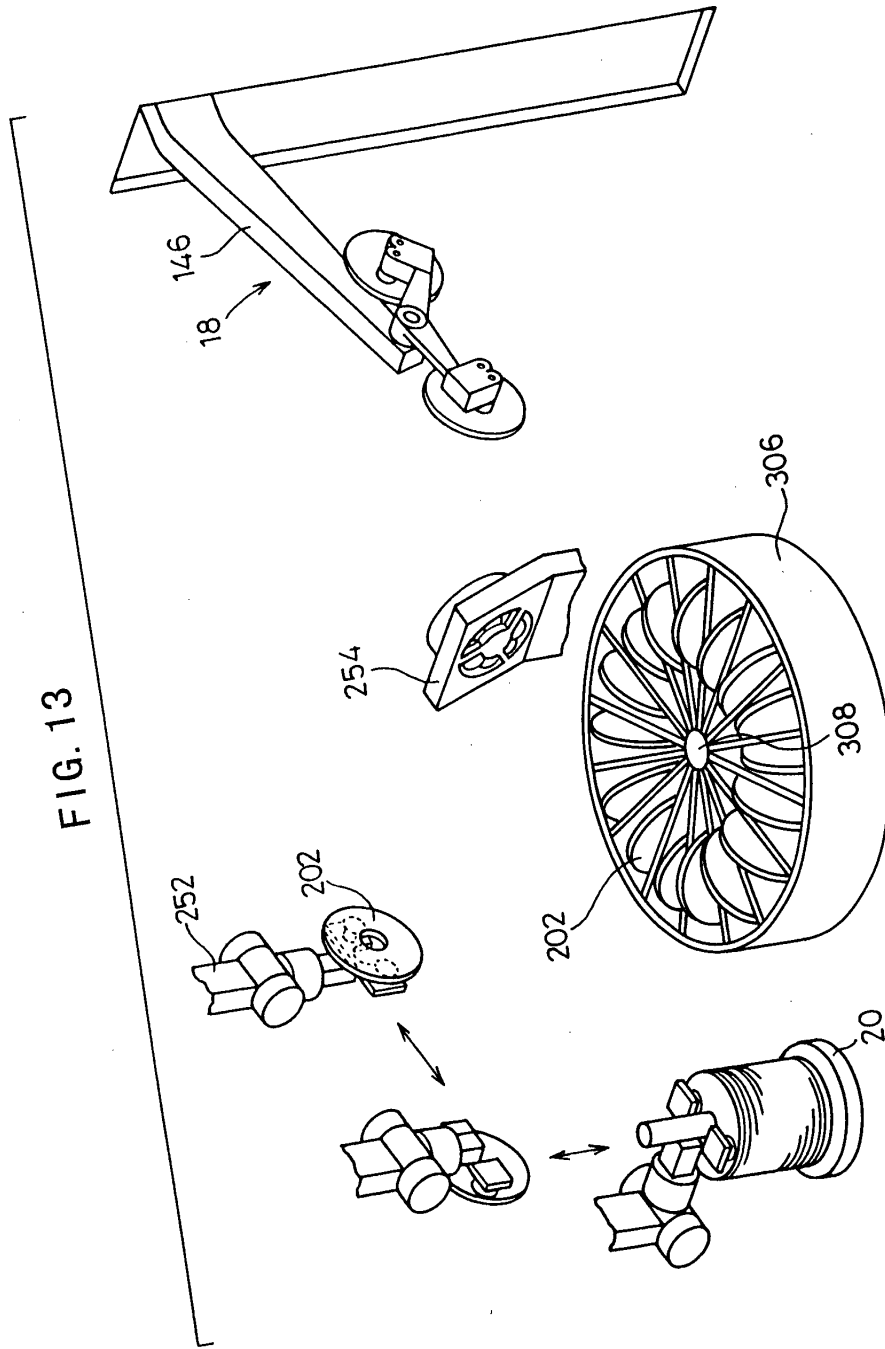


FIG. 14

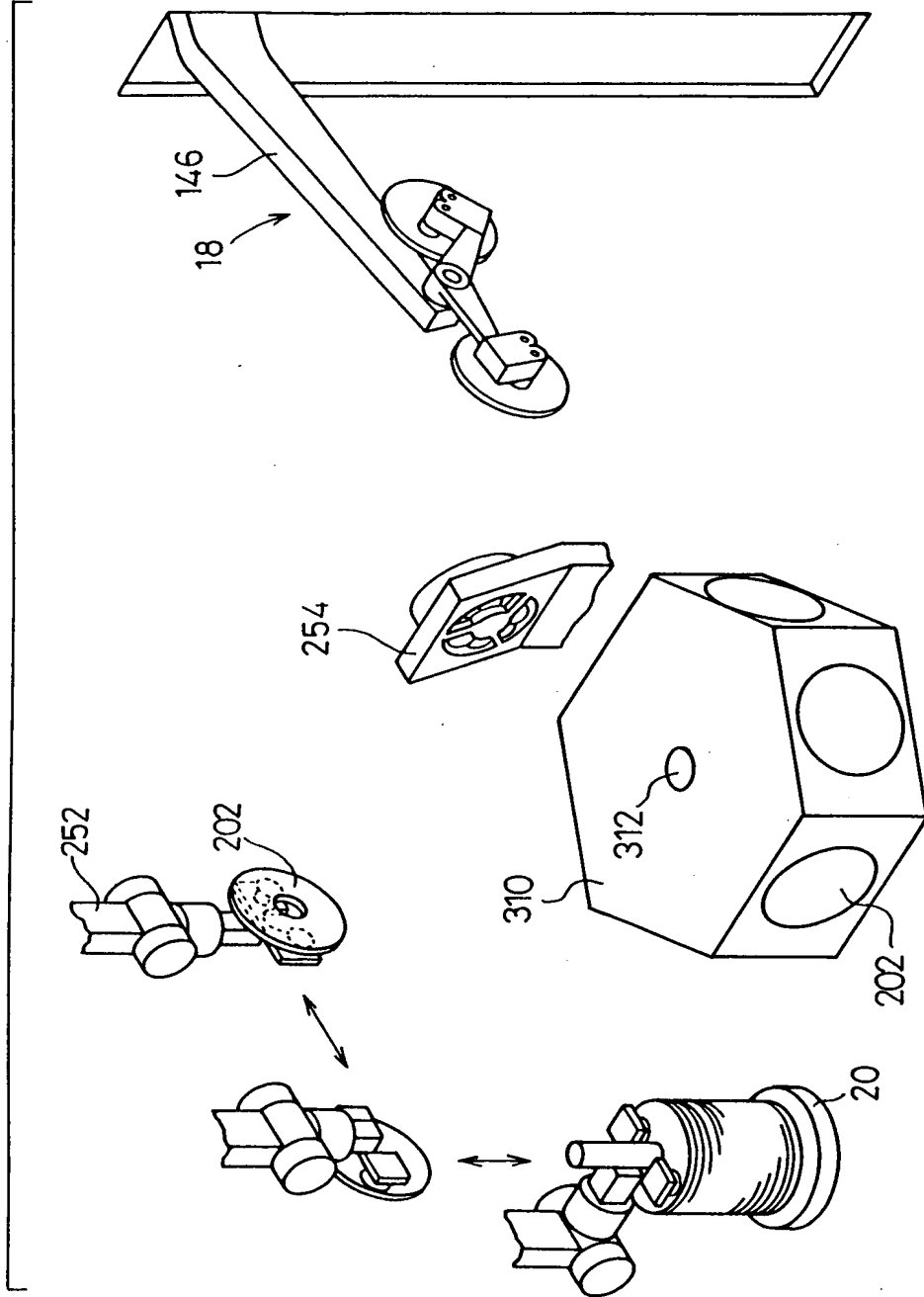


FIG. 15

